





S3D08065A S3D08065E S3D08065G 650V SIC POWER SCHOTTKY RECTIFIERS

Description

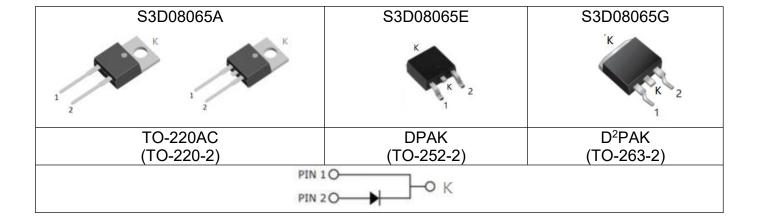
S3D08065A/S3D08065E/S3D08065G are SiC Schottky rectifiers packaged in TO-220AC(TO-220-2)/DPAK(TO-252-2)/D2PAK(TO-263-2) case. The devices are high voltage Schottky rectifiers that have very low total conduction losses and very stable switching characteristics over temperature extremes. The S3D08065A/S3D08065E/S3D08065G are ideal for energy sensitive, high frequency applications in challenging environments.

Applications

- · Alternative energy inverters
- Power Factor Correction (PFC)
- Free-Wheeling diodes
- · Switching supply output rectification
- Reverse polarity protection

Features

- 175°C T_J operation
- Ultra-low switching loss
- Switching speeds independent of operating temperature
- Low total conduction losses
- · High forward surge current capability
- High package isolation voltage
- Terminals finish: 100% Pure Tin
- "-A" is an AEC-Q101 qualified device
- Pb Free Device
- . All SMC parts are traceable to the wafer lot
- Additional electrical and life testing can be performed upon request









Maximum Ratings

Characteristics	Symbol	Condition	Max.	Units
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V _{RRM} V _{RWM} V _{DC}	-	650	V
-	I _{F (AV)1}	Tc=25°C	23	Α
Average Rectified Forward Current	I _{F (AV)2}	Tc=136°C	11	Α
	I _{F (AV)3}	Tc=157°C	8	А
Repetitive Peak Forward Surge Current	I _{FRM1}	10ms, Half Sine pulse, T _J =25°C	37.5	Α
	I _{FRM2}	10ms, Half Sine pulse, T _J =110°C	25.5	А
Peak One Cycle Non-Repetitive Surge Current	I _{FSM1}	10ms, Half Sine pulse, T _J =25°C	71	Α
	I _{FSM2}	10ms, Half Sine pulse, T _J =110°C	60	Α
Non-Repetitive Peak Forward Surge Current	I _{F,Max}	10µs. Pulse, T₁=25°C	650	Α
Non-Repetitive Feak Forward Surge Current	I _{F,Max}	10µs. Pulse, T₃=110°C	530	А
B	P _{tot1}	T _J =25°C	100	W
Power Dissipation	P _{tot1}	T _J =110°C	43.5	W
TO 000 Marrier Tarrer		M3 Screw	1	Nm
TO-220 Mounting Torque		6-32 Screw	8.8	bf-in

Electrical Characteristics:

Characteristics	Symbol	Condition	Тур.	Max.	Units
Forward Voltage Drop*	V_{F1}	@ 8A, Pulse, T _J = 25 °C	1.5	1.8	V
	V _{F2}	@ 8A, Pulse, T _J = 175 °C	2.1	2.4	V
Reverse Current*	I _{R1}	$@V_R = \text{rated } V_R$ $T_J = 25 ^{\circ}\text{C}$	0.5	51	uA
	I _{R2}	$@V_R = \text{rated } V_R$ $T_J = 175 ^{\circ}\text{C}$	12	204	uA
Junction Capacitance	Ст	VR=0V, Tj=25℃,f=1MHz	661	-	pF
Reverse Recovery Charge	Qc	I _F = 8A, di/dt = 200A/μs VR = 400 V, T _J =25°C	20	-	nC
Capacitance Stored Energy	E c	V _R = 400 V	3.1	-	μͿ

^{*} Pulse width < 300 µs, duty cycle < 2%

Thermal-Mechanical Specifications:

Characteristics	Symbol	S3D08065A	S3D08065E	S3D08065G	Units
Junction Temperature	TJ		-55 to +175		°C
Storage Temperature	T _{stg}	-55 to +175			°C
Typical Thermal Resistance Junction to Case	R _{qJC}	1.7	1.5	1.65	°C/W

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Ordering Information

Device	Package	Shipping
S3D08065A	TO-220AC(TO-220-2)	50pcs / tube
S3D08065E	DPAK(TO-252-2)	2500pcs / reel
S3D08065ETR	DPAK(TO-252-2)	2500pcs / reel
S3D08065G	D2PAK(TO-263-2)	800 pcs / reel
S3D08065GTR	D2PAK(TO-263-2)	800 pcs / reel

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our tape and reel packaging specification.

Ratings and Characteristics Curves

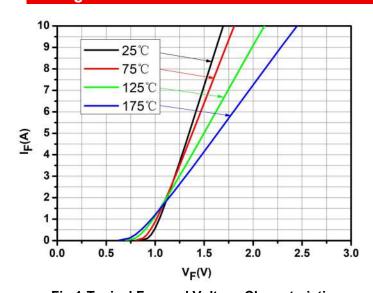


Fig.1-Typical Forward Voltage Characteristics

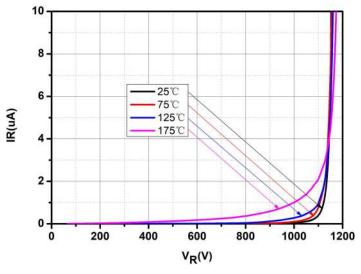


Fig.2-Typical Reverse Characteristics

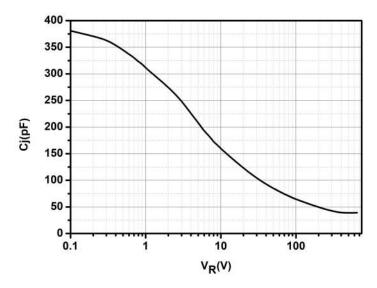


Fig.3-Capacitance vs. Reverse Voltage

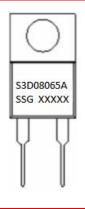
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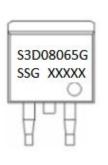




Marking Diagram







Where XXXXX is YYWWL

S3D = Device Type
A/E/G = Package type
08 = Forward Current (8A)
65 = Reverse Voltage (650V)

 SSG
 = SSG

 YY
 = Year

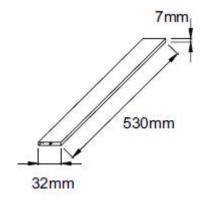
 WW
 = Week

 L
 = Lot Number

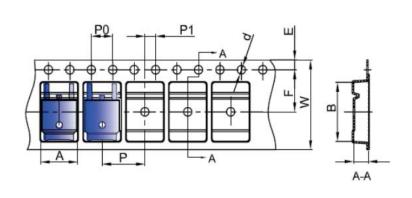
Cautions: Molding resin

Epoxy resin UL:94V-0

Tube Specification(TO-220-2)



Carrier Tape & Reel Specification DPAK(TO-252-2)



SYMBOL	Millimeters		
STWIBOL	Min.	Max.	
Α	6.80	7.00	
В	10.40	10.60	
С	2.60	2.80	
d	Ф1.45	Ф1.65	
E	1.65	1.85	
F	7.40	7.60	
P0	3.90	4.10	
Р	7.90	8.10	
P1	1.90	2.10	
W	15.90	16.30	

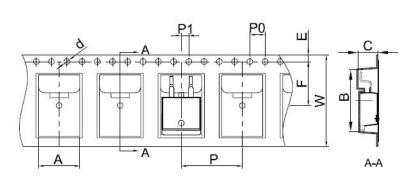
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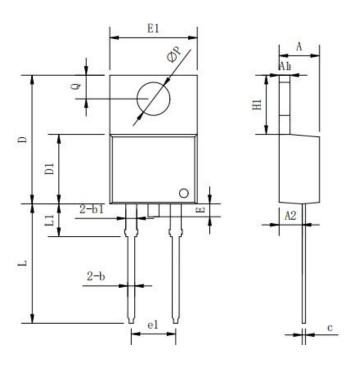


Carrier Tape & Reel Specification D2PAK(TO-263-2)



SYMBOL	Millimeters		
	Min.	Max.	
Α	10.70	10.90	
В	16.03	16.23	
С	5.11	5.31	
d	1.45	1.65	
E	1.65	1.85	
F	11.40	11.60	
P0	3.90	4.10	
Р	15.90	16.10	
P1	1.90	2.10	
W	23.90	24.30	

Mechanical Dimensions TO-220AC(TO-220-2)



Symbol	Dimensions in millimeters			
,	Min.	Typical	Max.	
Α	3.56	-	4.83	
A1	0.51	-	1.40	
A2	2.03	-	2.92	
b	0.38	-	1.02	
b1	1.14	-	1.78	
С	0.31	-	0.61	
D	14.22	-	16.51	
D1	8.38	-	9.42	
E	-	-	1.78	
E1	9.65	10.16	10.67	
e1	-	5.08	-	
H1	5.84	-	6.86	
L	12.70	-	14.73	
L1	_	-	6.35	
ФР	-	3.56	-	

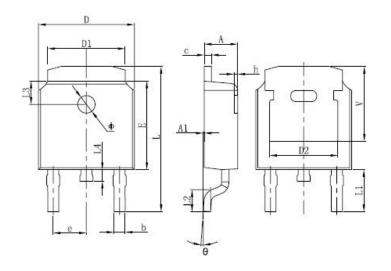
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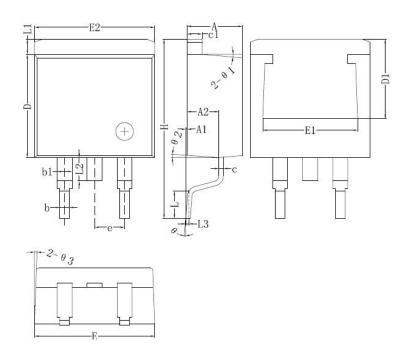


Mechanical Dimensions DPAK(TO-252-2)



SYMBOL	Dimensions in millimeters			
	Min.	Тур.	Max.	
Α	2.18	-	2.39	
A1	-	-	0.13	
b	0.64	-	0.89	
С	0.46	-	0.89	
D	6.35	-	6.73	
D2	4.32	-	-	
E	5.97	6.10	6.22	
е		2.29BSC		
L	9.40	-	10.41	
L2	1.40	1.52	1.78	
L4	-	-	1.02	
Θ	0°	-	10°	
V	5.21	-	-	

Mechanical Dimensions D²PAK(TO-263-2)



Symbol	Dimensions in millimeters		
- Cynnson	Min.	Max.	
А	4.06	4.83	
A1	0	0.26	
b	0.51	0.99	
b1	1.14	1.78	
С	0.31	0.74	
c1	1.14	1.65	
D	8.38	9.65	
D1	6.86		
E1	6.22		
E2	9.65	10.67	
е	2.54BSC		
Н	14.60	15.88	
L	1.78	2.80	
L1	-	1.68	
L2	-	2.20	
L3	0.255BSC		
Θ	0	8°	

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